

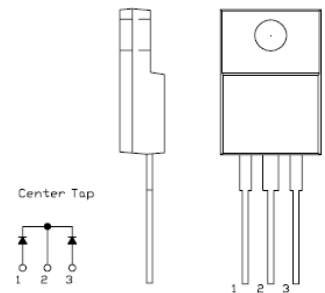
SBRF10150CT SCHOTTKY RECTIFIER

Applications:

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

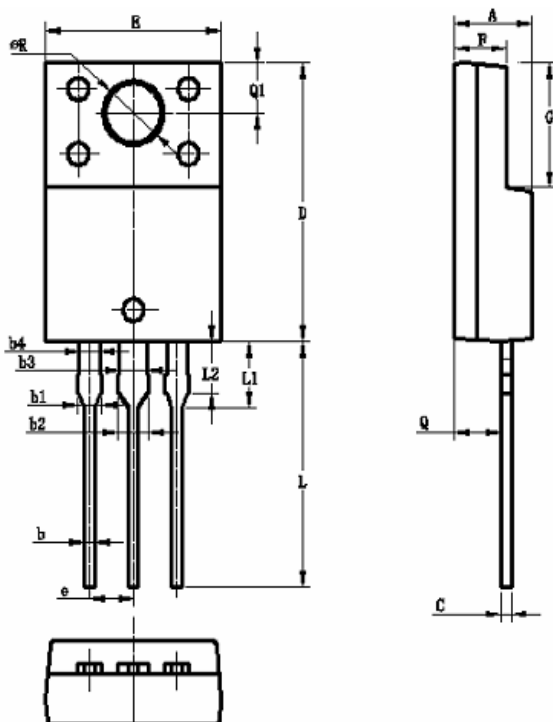
Features:

- 150°C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

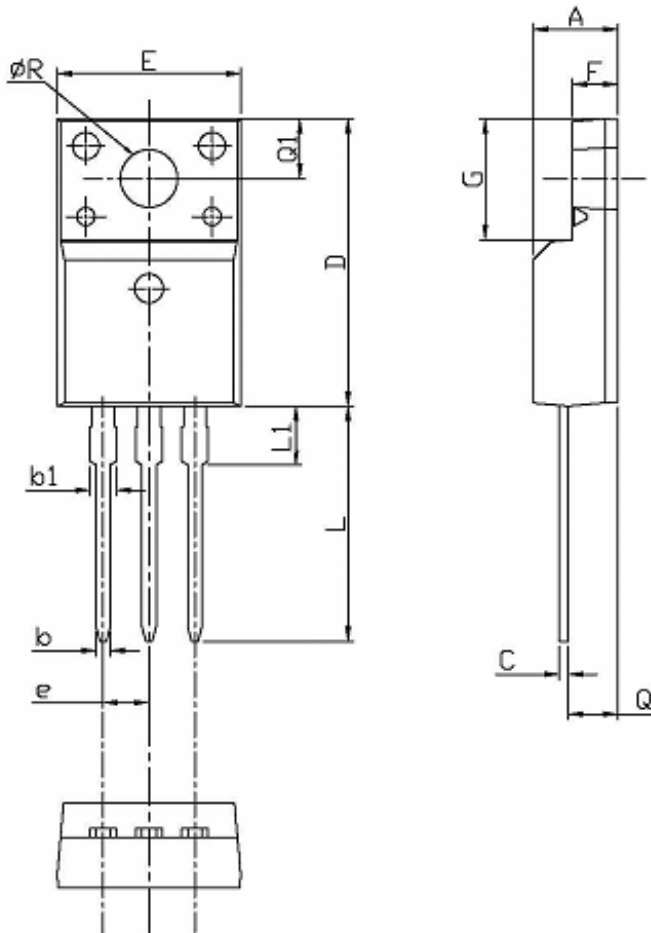


OUTLINE DRAWING

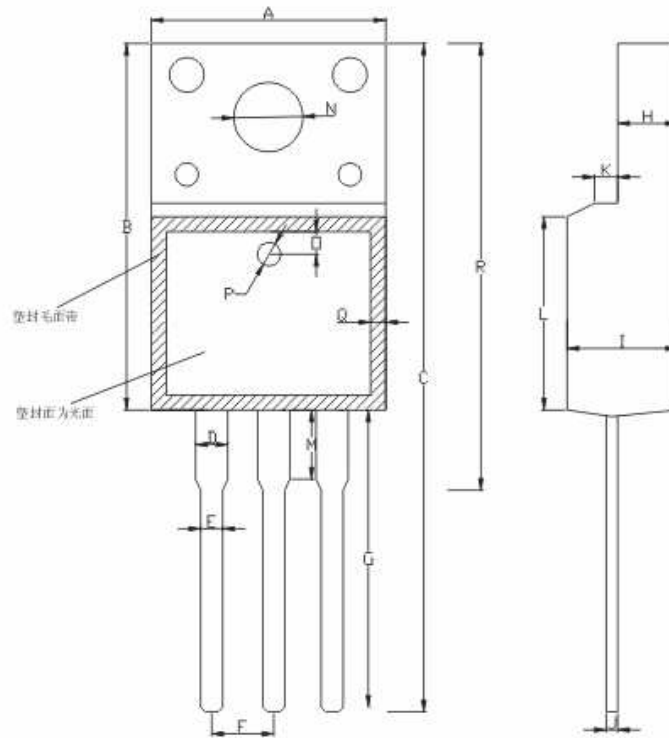
Mechanical Dimensions: In mm



Dim	OPTION 1(CJ)		OPTION 2(HD)	
	Min	Max	Min	Max
A	4.4	4.6	4.30	4.70
b	0.6TYP		0.50	0.75
b1	1.3TYP		1.30	1.40
b2	1.7TYP		1.70	1.80
b3	1.6TYP		1.50	1.75
b4	1.2TYP		1.10	1.35
C	0.60TYP		0.50	0.75
D	14.8	15.1	14.80	15.20
E	10.06	10.26	9.96	10.36
e	2.55TYP		2.54TYP	
F	2.9	3.1	2.80	3.20
G	6.5	6.9	6.50	6.90
L	12.7	13.7	12.8	13.2
L1	3.4	3.8	3.60	4.00
L2	2.6	3.0	-	-
Q	2.5	2.9	2.50	2.90
Q1	2.5	2.9	2.70REF	
ØR	3.5REF		3.50REF	



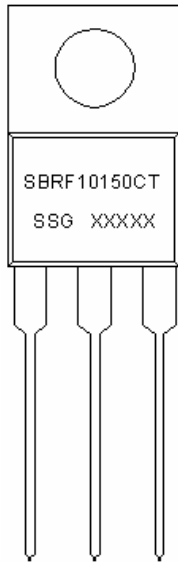
Dim	OPTION 3		OPTION 4	
	Min	Max	Min	Max
A	4.53	4.93	4.50	4.90
b	0.71	0.91	0.70	0.90
b1	1.15	1.39	1.33	1.47
C	0.36	0.53	0.45	0.60
D	15.67	16.07	15.67	16.07
E	9.96	10.36	9.96	10.36
e	2.54 TYP		2.54 BSC	
F	2.34	2.76	2.34	2.74
G	6.50	6.90	6.48	6.88
L	12.37	12.77	12.78	13.18
L1	2.23	2.63	3.03	3.43
Q	2.56	2.96	2.56	2.96
Q1	3.10	3.50	3.10	3.50
ϕR	2.98	3.38	3.08	3.28



A:10.20 ± 0.50	B:15.90 ± 0.50	C:29.00 ± 1.00	D:1.24 ± 0.10
E:0.80 ± 0.10	F:2.54 ± 0.10	G:13.10 ± 1,0	H:2.55 ± 0.05
I:4.70 ± 0.05	J:0.50 ± 0.05	K:1.20 ± 0.20	L:8.00 ± 0.50
M:3.00 ± 0.50	N:3.20 ± 0.20	O:1,25 ± 0.05	P:1.5 ± 0.05
Q:1.0 ± 0.20	R:19.2 ± 1.0		

OPTION 5 (SR)

ITO-220AB

Marking Diagram:


Where XXXXX is YYWWL

SBR	= Device Type
F	= Package type
10	= Forward Current (10A)
150	= Reverse Voltage (150V)
CT	= Configuration
SSG	= SSG
YY	= Year
WW	= Week
L	= Lot Number

Cautions: Molding resin
 Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
SBRF10150CT	ITO-220AB (Pb-Free)	50pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	150	V
Max. Average Forward	$I_{F(AV)}$	50% duty cycle @ $T_C = 145^\circ\text{C}$, rectangular wave form	10	A
Max. Peak One Cycle Non-Repetitive Surge Current (per leg)	I_{FSM}	8.3 ms, half Sine pulse	120	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop (per leg) *	V_{F1}	@ 5 A, Pulse, $T_C = 25\text{ }^\circ\text{C}$	0.93	V
Max. Reverse Current (per leg) *	I_{R1}	@ $V_R = \text{rated } V_R$ $T_C = 25\text{ }^\circ\text{C}$	1.0	mA
Max. Junction Capacitance (per leg)	C_T	@ $V_R = 5\text{V}$, $T_C = 25\text{ }^\circ\text{C}$ $f_{SIG} = 1\text{MHz}$	200	pF
Typical Series Inductance (per leg)	L_S	Measured lead to lead 5 mm from package body	8.0	nH
Max. Voltage Rate of Change	dv/dt	-	10,000	V/ μs

* Pulse Width < 300 μs , Duty Cycle <2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Max. Junction Temperature	T_J	-	-55 to +150	$^\circ\text{C}$
Max. Storage Temperature	T_{stg}	-	-55 to +150	$^\circ\text{C}$
Maximum Thermal Resistance Junction to Case	$R_{\theta JC}$	DC operation	4.5	$^\circ\text{C/W}$
Approximate Weight	wt	-	2	g
Case Style	ITO-220AB			

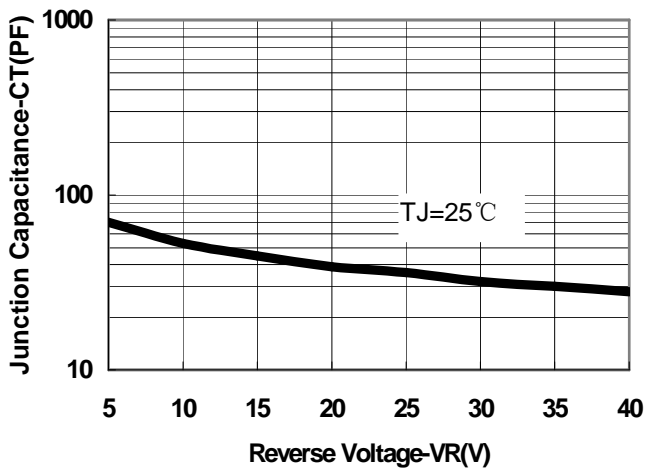


Fig.1-Typical Junction Capacitance

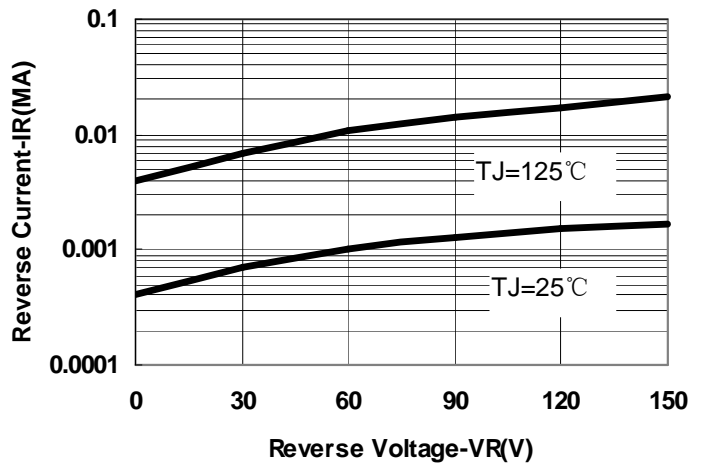


Fig.2-Typical Reverse Characteristics

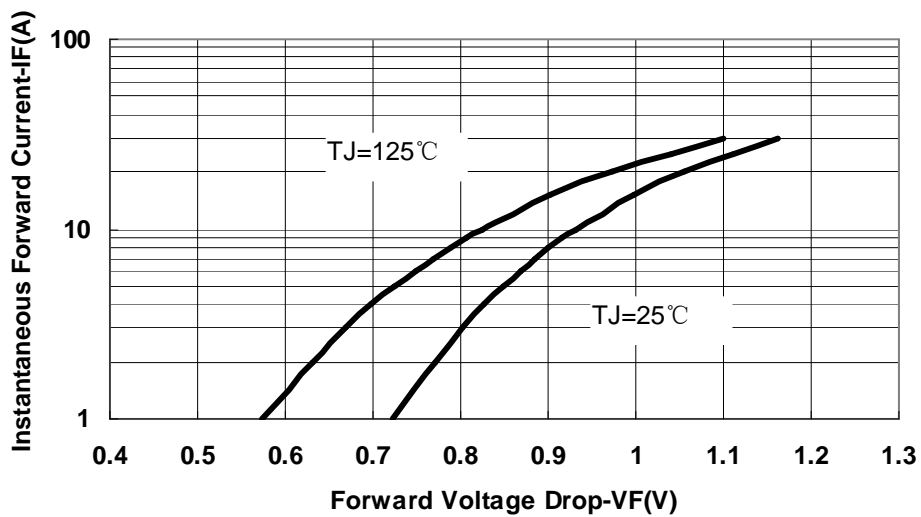


Fig.3-Typical Instantaneous Forward Voltage Characteristics

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